

MOS FIELD EFFECT TRANSISTOR



Features

- Low gate charge
- $Q_g = 30 \text{ nC TYP. (VDD} = 400 \text{ V, VGS} = 10 \text{ V, ID} = 12 \text{ A)}$
- Gate voltage rating $\pm 30 \text{ V}$
- Low on-state resistance
- $R_{DS(on)} = 0.60 \text{ Ohms MAX. (@ VGS} = 10 \text{ V, ID} = 6.0 \text{ A)}$
- Avalanche capability rating
- Surface mount package available
- Package: TO-252